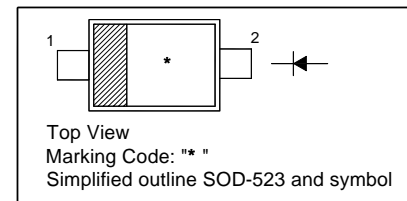


### Silicon Epitaxial Planar Schottky Barrier Diode

for high speed switching application

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

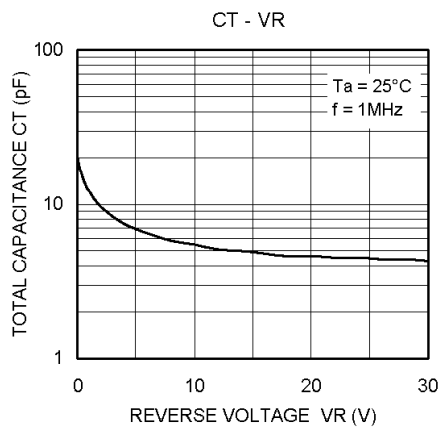
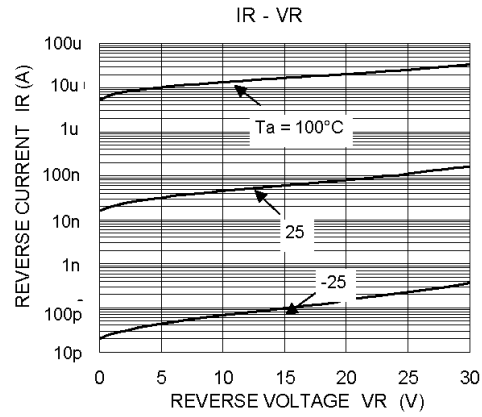
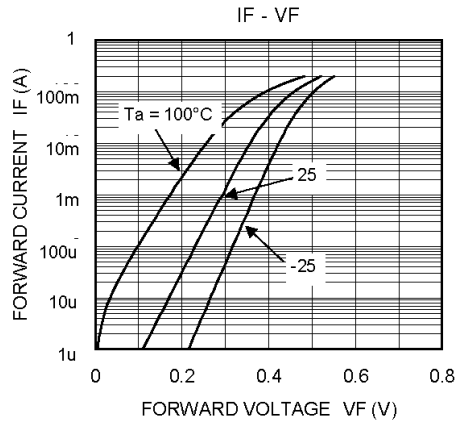


#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	35	V
Reverse Voltage	$V_R$	30	V
Average Forward Current	$I_{F(AV)}$	200	mA
Peak Forward Current	$I_{FM}$	300	mA
Power Dissipation	$P_{tot}$	150	mW
Surge Current (10 ms)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Operating Temperature Range	$T_{opr}$	- 40 to + 100	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

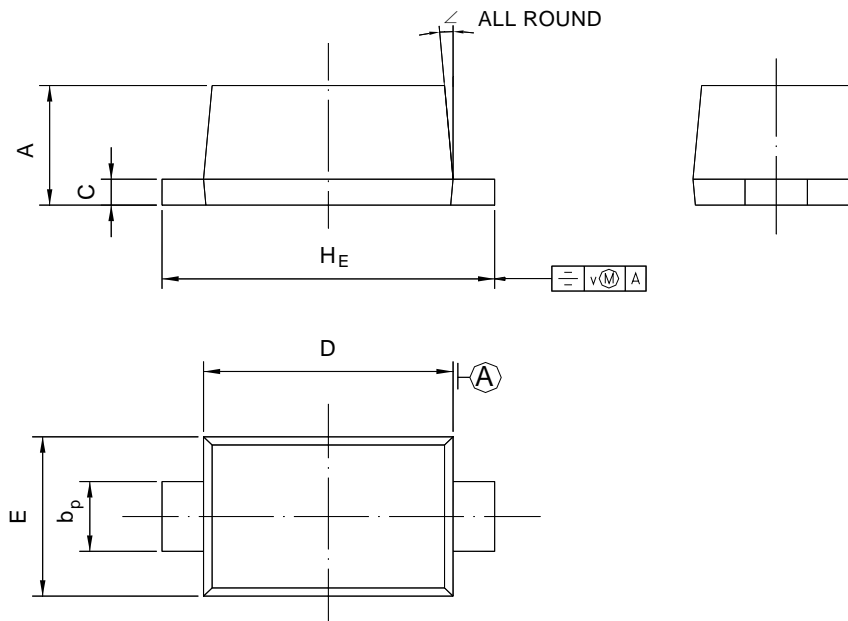
Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	-	0.6	V
Reverse Current at $V_R = 30\text{ V}$	$I_R$	-	5	$\mu\text{A}$
Total Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	20	-	pF



### PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b <sub>p</sub>	C	D	E	H <sub>E</sub>	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°